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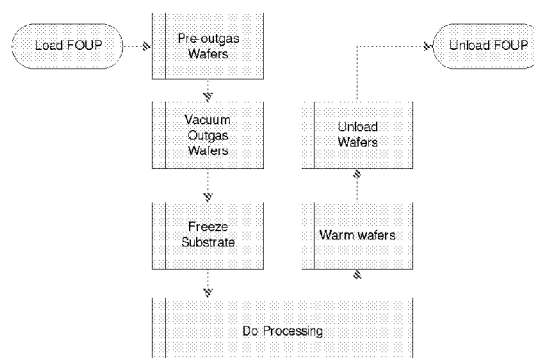


Fig. 22

(57) **Abstract:** A method of processing a substrate (1) that displays out-gassing when placed in a vacuum comprises placing the substrate in a vacuum and performing an out-gassing treatment by heating the substrate (1) to a temperature T1 and removing gaseous contamination emitted from the substrate (1) until the out-gassing rate is determined by the diffusion of the substrate's contamination and thus essentially a steady state has been established. Afterwards, the temperature is lowered to a temperature T2 at which the diffusion rate of the substrate's contamination is lower than at T1. The substrate (1) is further processed at said temperature T2 until the substrate (1) has been covered with a film (16) comprising a metal.